

## CORRECTION

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## Correction: Epitaxial growth of $\beta\text{-Ga}_2\text{O}_3$ ( $-201$ ) thin film on four-fold symmetry $\text{CeO}_2$ (001) substrate for heterogeneous integrations

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Correction for 'Epitaxial growth of  $\beta\text{-Ga}_2\text{O}_3$  ( $-201$ ) thin film on four-fold symmetry  $\text{CeO}_2$  (001) substrate for heterogeneous integrations' by Xiao Tang et al., *J. Mater. Chem. C*, 2021, **9**, 15868–15876, DOI: 10.1039/D1TC02852A.

The authors regret the omission of the email address for the co-corresponding author, Xiaohang Li, from the original published article. Their email address is [Xiaohang.li@kaust.edu.sa](mailto:Xiaohang.li@kaust.edu.sa), and the corrected author affiliation details are shown here.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.



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